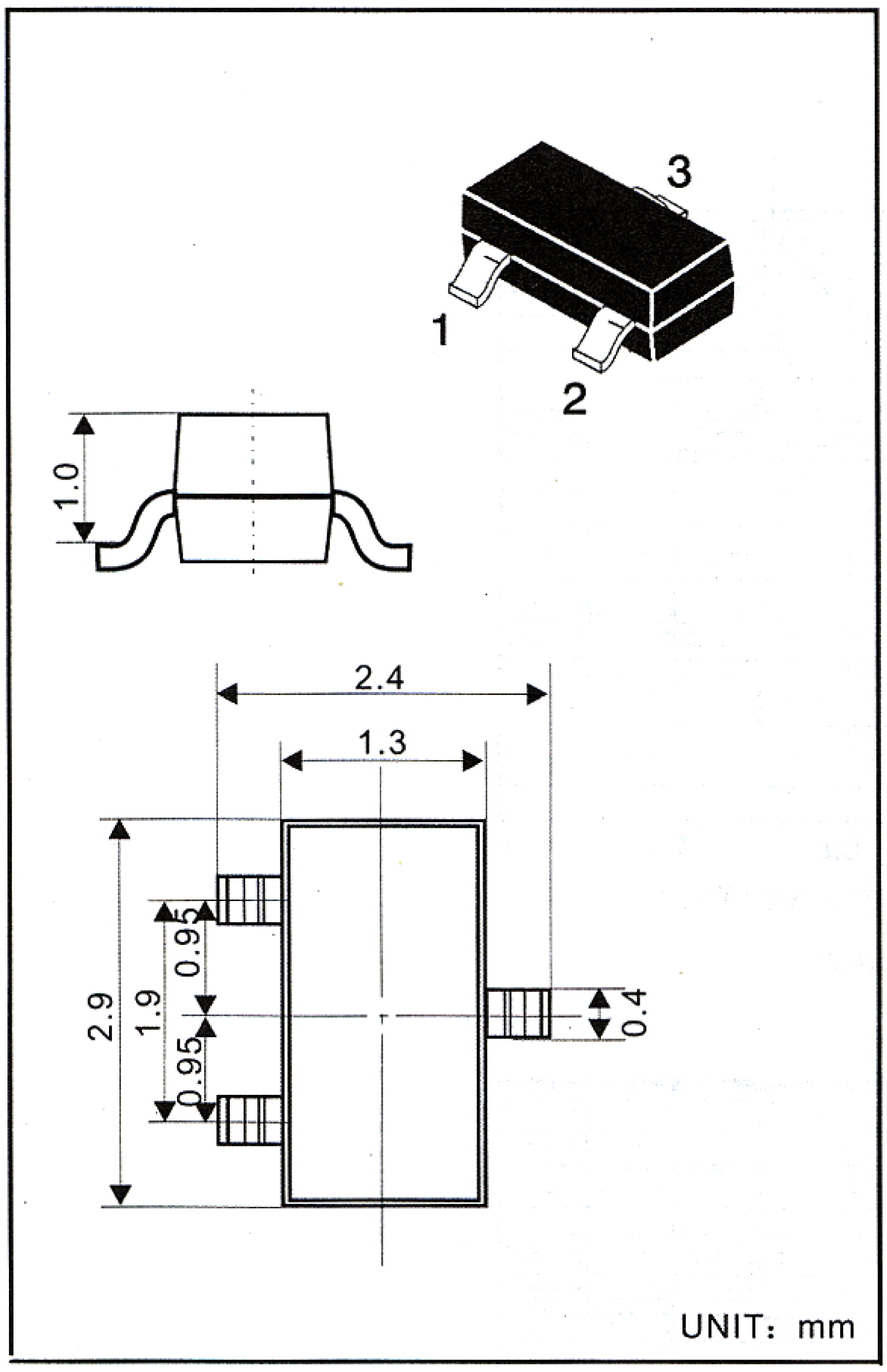
SOT-23 Plastic-Encapsulate DIODES

BAS16LT1 SWITCHING DIODE



FEATURES

Power dissipation

P_D: 225mW（Tamb=25℃）

Forward current

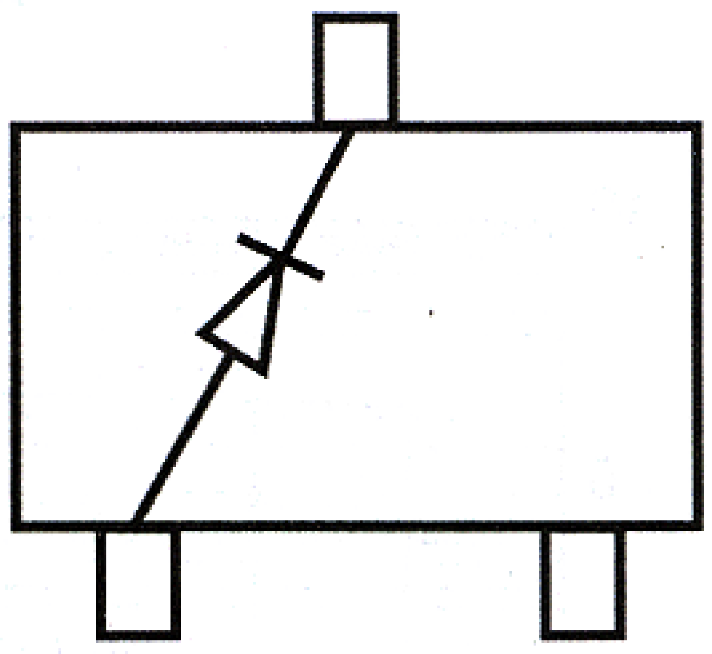
I_F: 200mA

Reverse voltage

V_R: 75V

Operating and storage junction temperature range

T_J,T_{stg} :-55℃ to+150℃



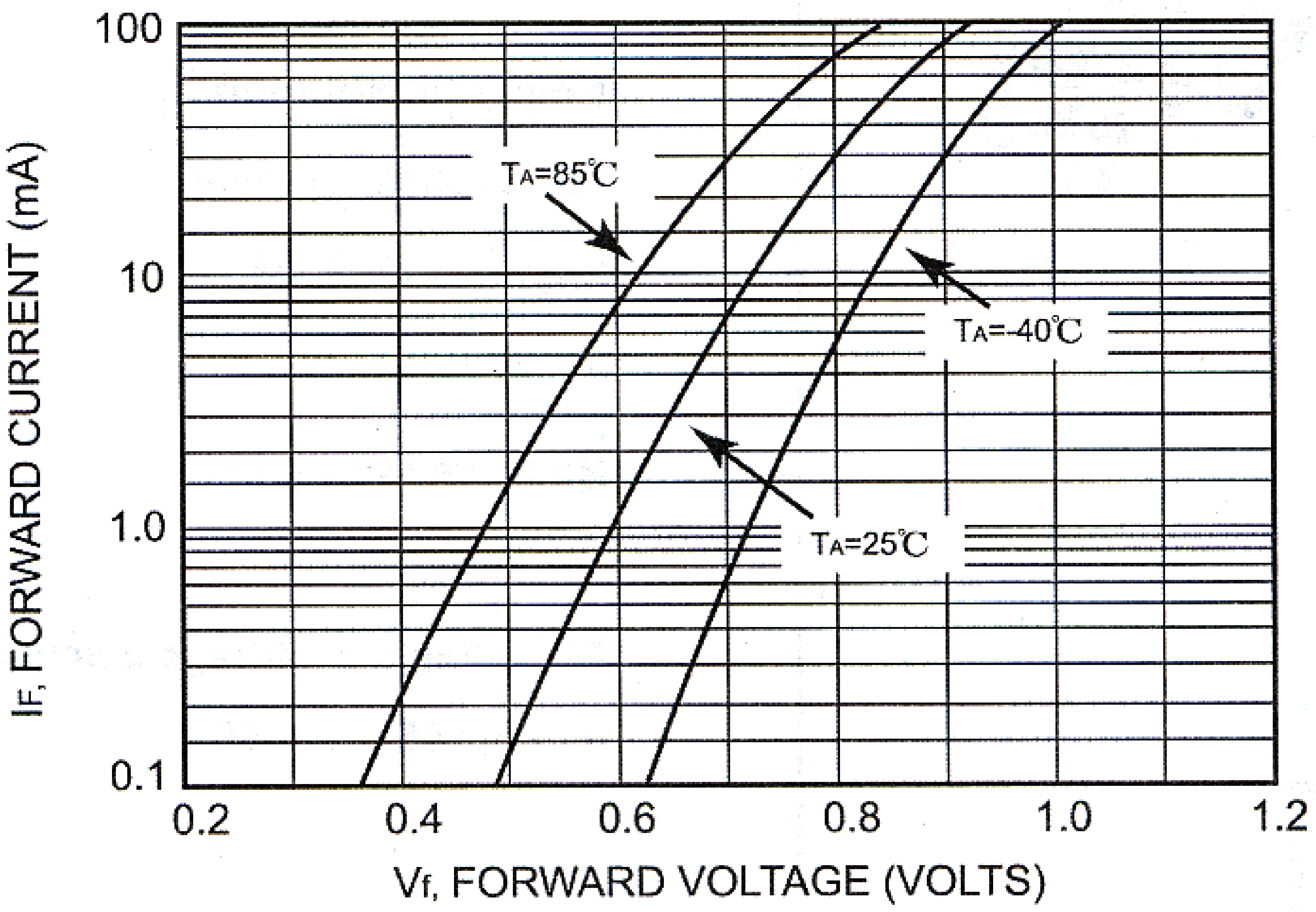
MARKING: A6

ELECTRICAL CHARACTERISTICS

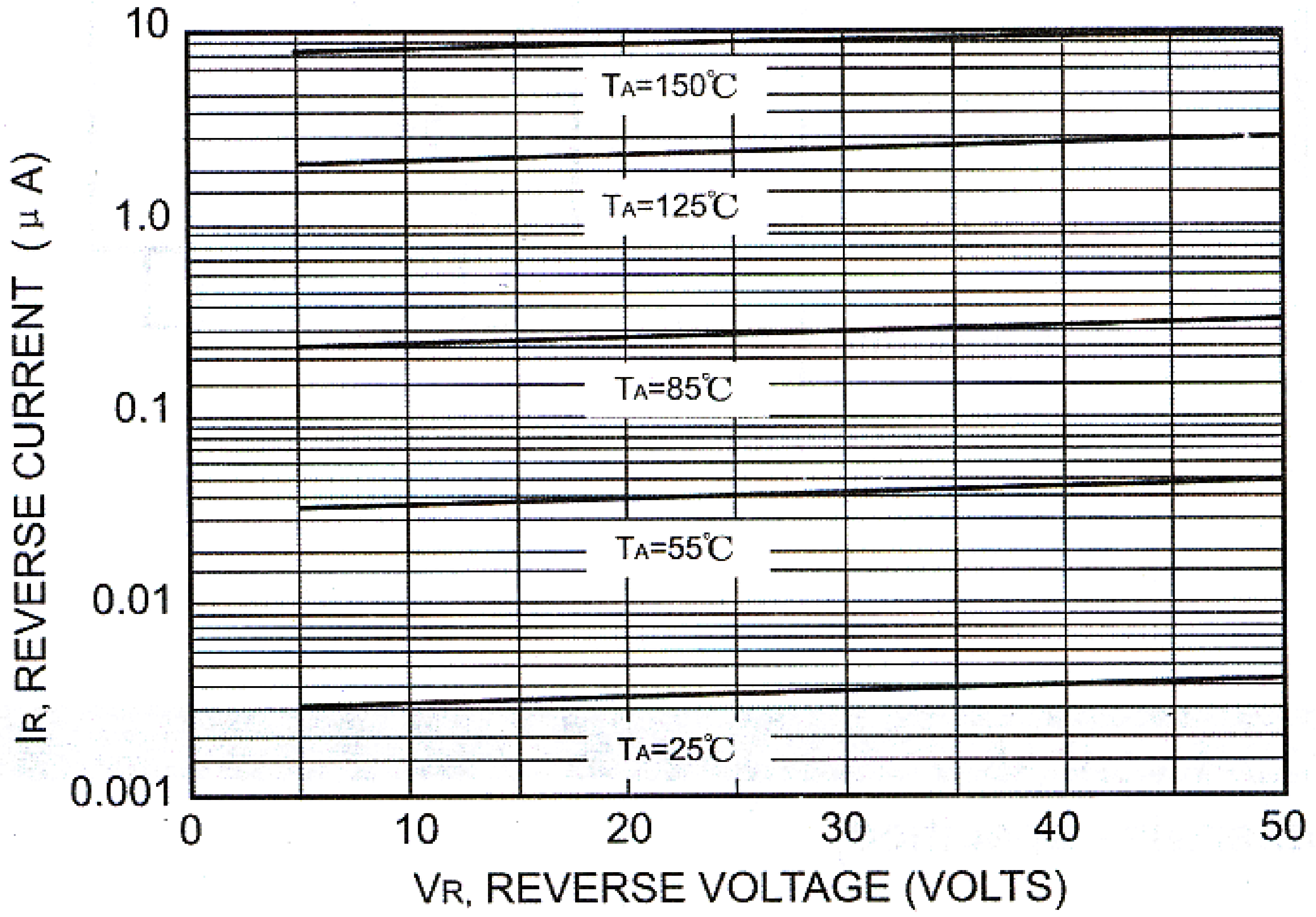
(Tamp=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	I_R=100μA	75		V
Reverse voltage leakage current	I_R	V_R=75V		1	μA
Forward voltage	V_F	I_F=1mA I_F=10mA I_F=50mA I_F=150mA		750 855 1000 1250	mV
Diode capacitance	C_{tot}	V_R=0V, f=1MHz		2	pF
Reverse recovery time	t_{rr}	I_F=I_R=10mA I_{rr}=0.1I_R		6	ns

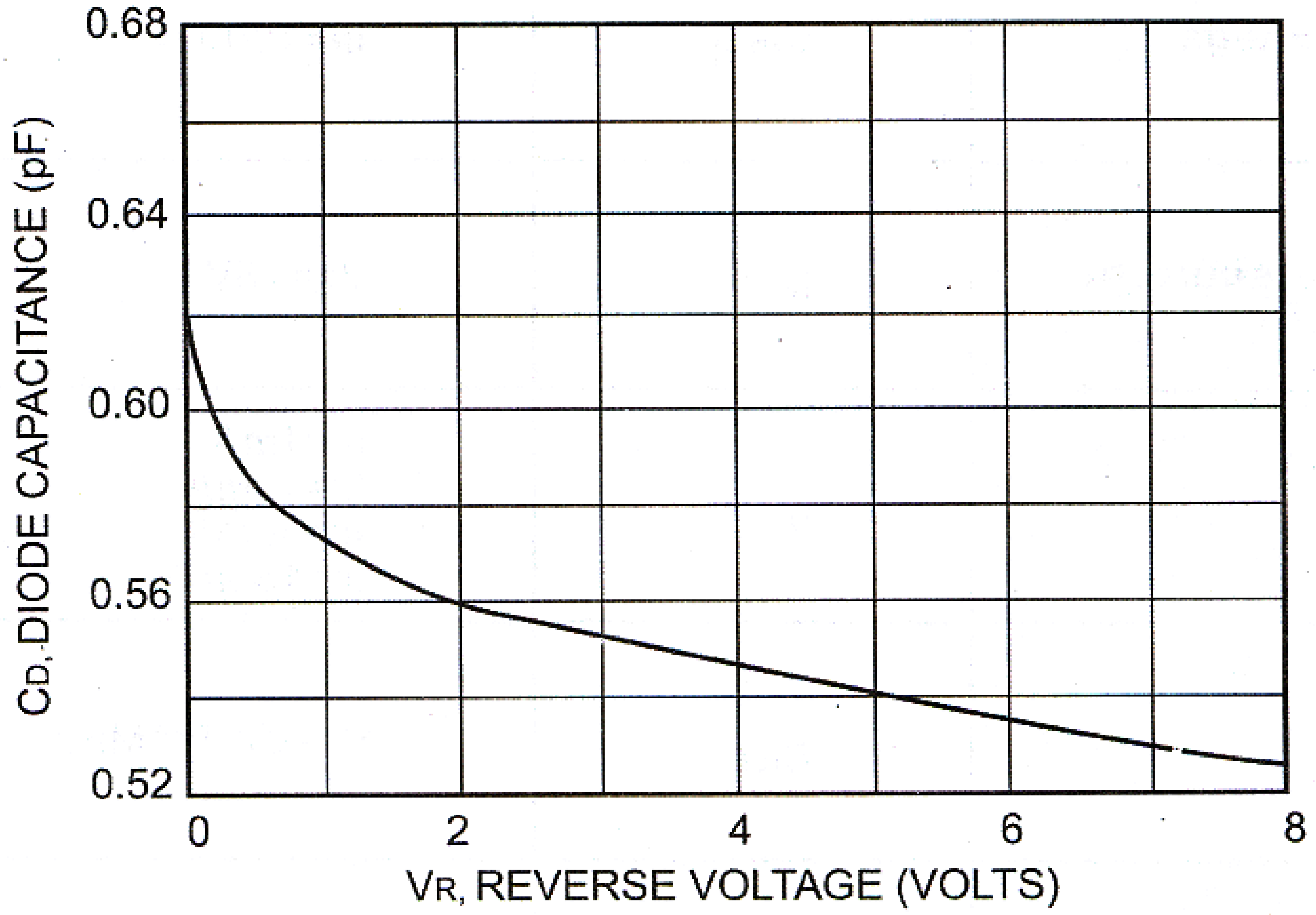
Typical Characteristics



Forward Voltage



Leakage Current



Capacitance